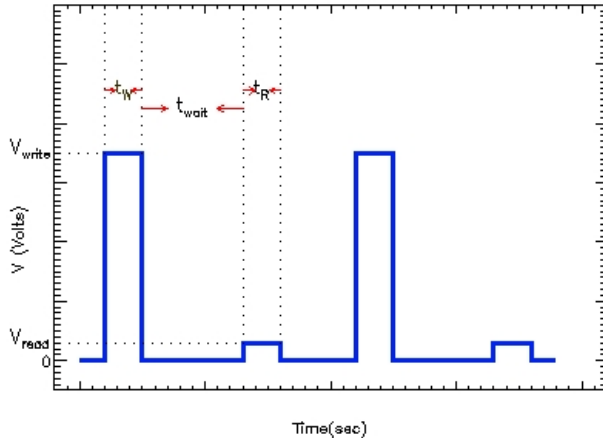


Resistive Switching in Sr2IrO4

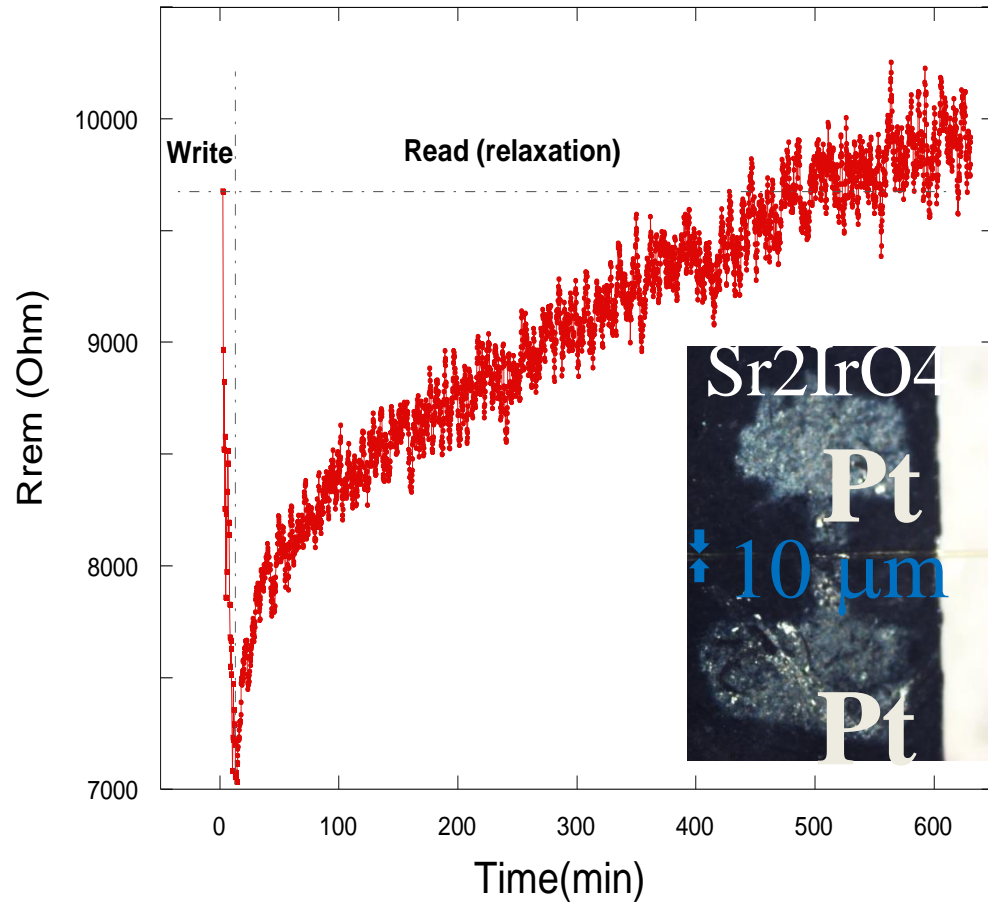
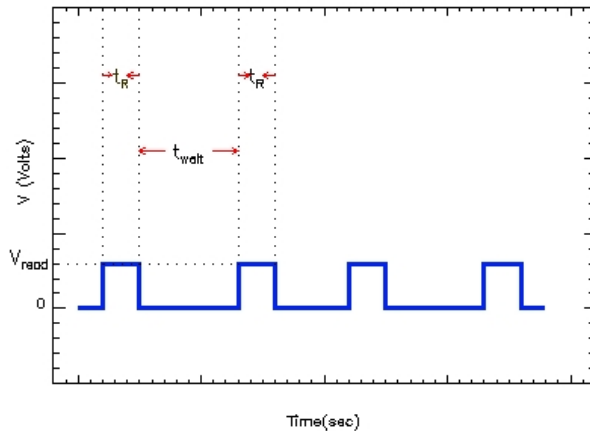
+Write & Read pulses:



Write: 3.5V – 1s / t_{wait} = 5–80 s

Read: 1V – 10 ms

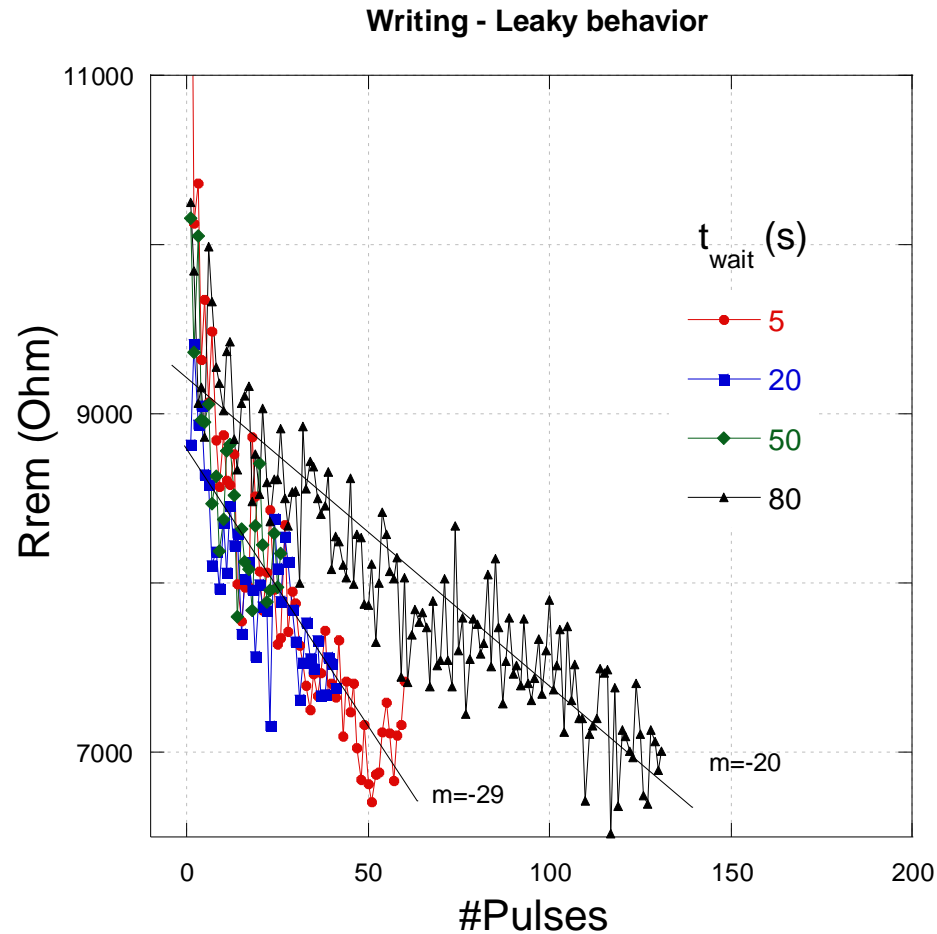
+Read pulses (relaxation):



- Cummulative effect of the write pulses
- Long relaxation (volatility)

Resistive Switching in Sr2IrO4

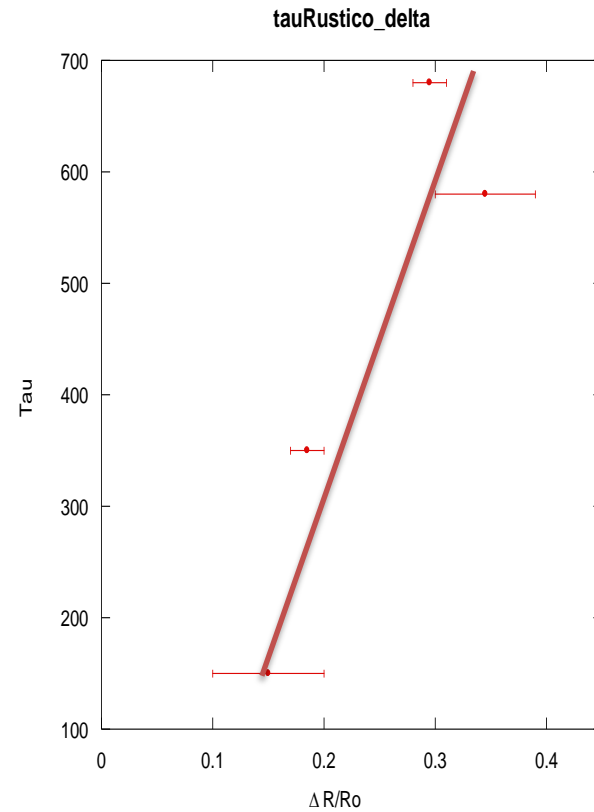
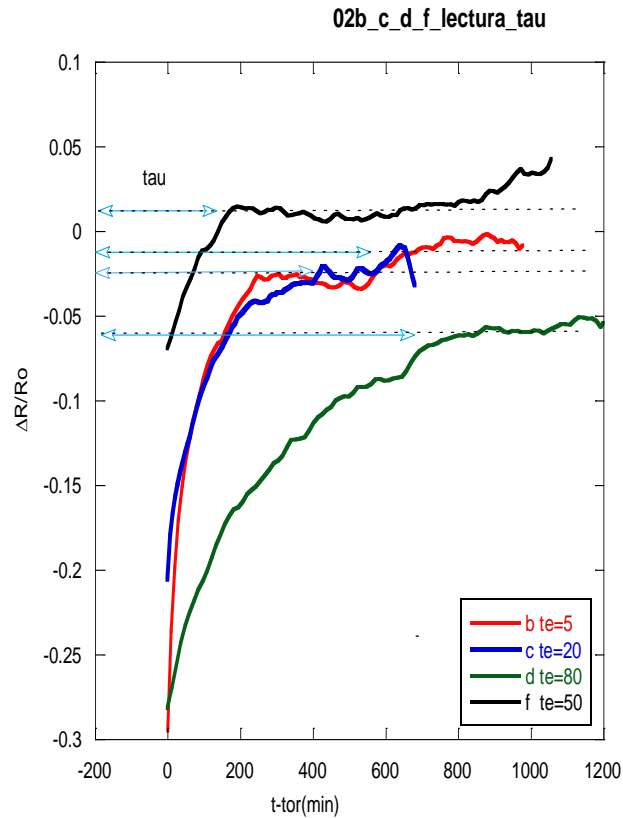
Relaxation studies: t_{wait} effect on writing



A leaky behavior can be observed

Resistive Switching in Sr2IrO4

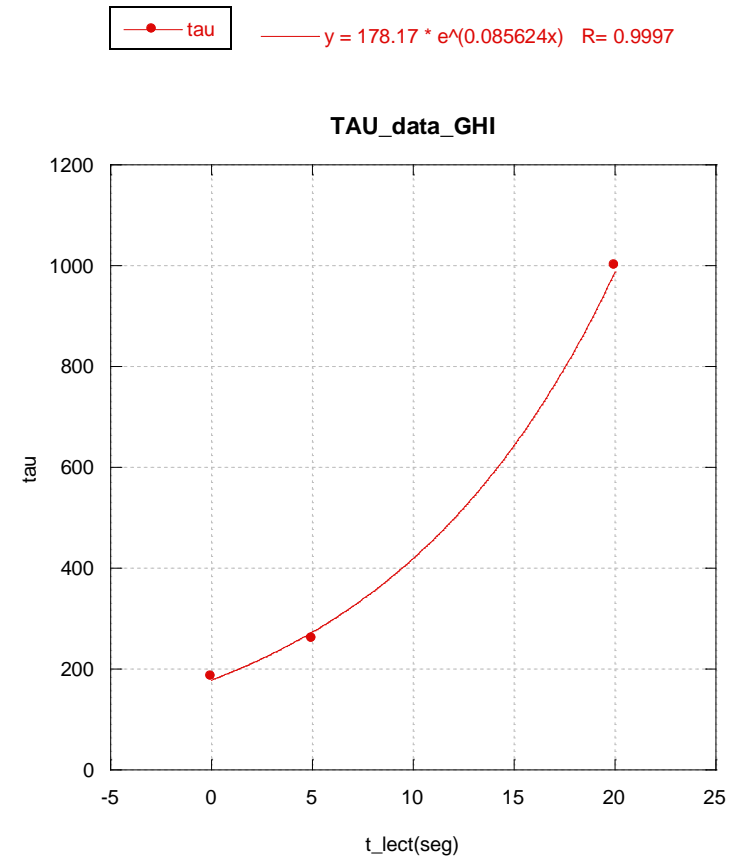
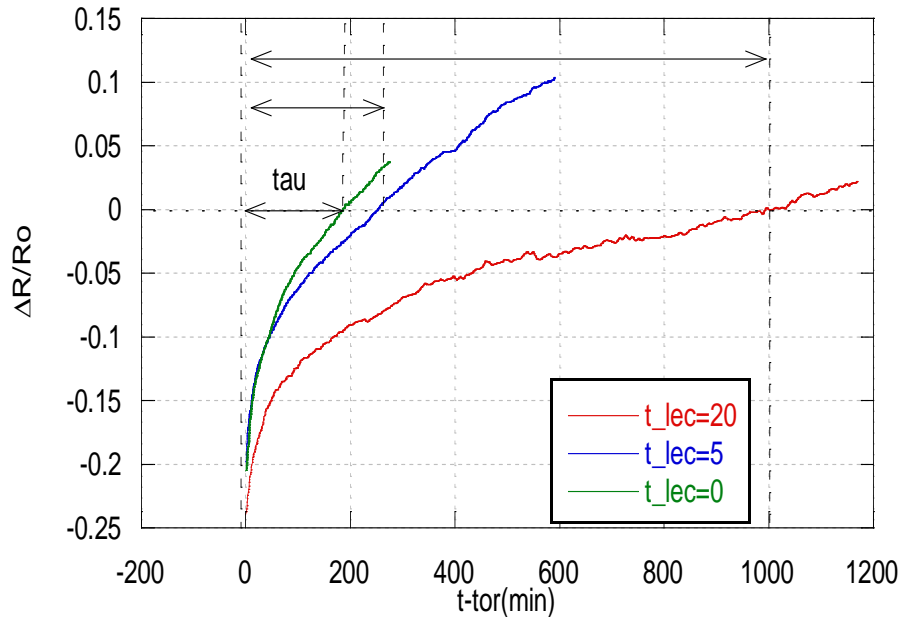
Relaxation studies: t_{wait} effect on writing



τ increases with increasing resistance change (ie with increasing the filament width)

Resistive Switching in Sr2IrO4

Relaxation studies: t_{wait} effect on reading



The frequency of reading pulses affects the relaxation process. Decreasing t_{wait} between readings reduces the relaxation time